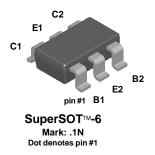


FMBA14



NPN Multi-Chip Darlington Transistor

This device is designed for applications requiring extremely high current gain at collector currents to 1.0 A. Sourced from Process 05.

Absolute Maximum Ratings* T_A = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V_{CES}	Collector-Emitter Voltage	30	V
V _{CBO}	Collector-Base Voltage	30	V
V _{EBO}	Emitter-Base Voltage	10	V
I _C	Collector Current - Continuous	1.2	A
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

^{*}These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

1) These ratings are based on a maximum junction temperature of 150 degrees C.
2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics T_A = 25°C unless otherwise noted

Symbol	Characteristic	Max	Units	
		FMBA14		
P _D	Total Device Dissipation	700	mW	
	Derate above 25°C	5.6	mW/°C	
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	180	°C/W	

NPN Multi-Chip Darlington Transistor

(continued)

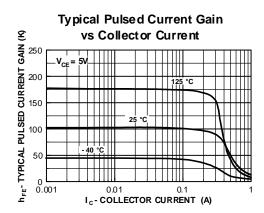
		<i>1</i> ' L		~+~	
FID(31)	11-21		-		
Electri	ıvaı	911	aı a	U.U	 ,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,,

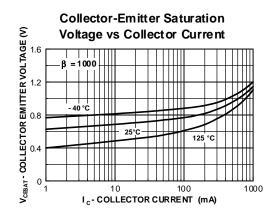
TA = 25°C unless otherwise noted

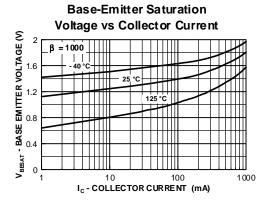
	Test Conditions	Conditions Min			Units				
CTERISTICS									
ollector-Emitter Breakdown Voltage	$I_C = 100 \mu\text{A}, I_B = 0$	30			V				
ollector-Cutoff Current	$V_{CB} = 30 \text{ V}, I_{E} = 0$			100	nA				
nitter-Cutoff Current	$V_{EB} = 10 \text{ V}, I_{C} = 0$			100	nA				
TERISTICS* C Current Gain	I_C = 10 mA, V_{CE} = 5.0 V I_C = 100 mA, V_{CE} = 5.0 V	10K 20K							
ollector-Emitter Saturation Voltage	$I_C = 100 \text{ mA}, V_C = 3.0 \text{ V}$		1.5	V					
ase-Emitter On Voltage	I _C = 100 mA, V _{CE} = 5.0 V			2.0	V				
$V_{BE(on)}$ Base-Emitter On Voltage $I_C = 100 \text{ mA}, V_{CE} = 5.0 \text{ V}$ 2.0 V SMALL SIGNAL CHARACTERISTICS h_{fe} Small Signal Current Gain $I_C = 10 \text{ mA}, V_{CE} = 5.0 \text{ V},$ 1.25 MHz									
	CHARACTERISTICS	CHARACTERISTICS	CHARACTERISTICS	CHARACTERISTICS	CHARACTERISTICS				

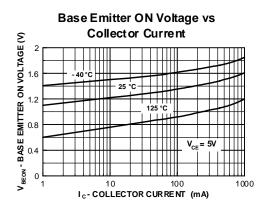
^{*}Pulse Test: Pulse Width ≤ 300 μs, Duty Cycle ≤ 2.0%

Typical Characteristics







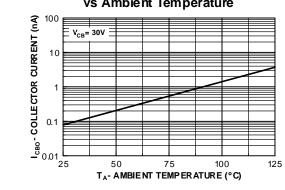


NPN Multi-Chip Darlington Transistor

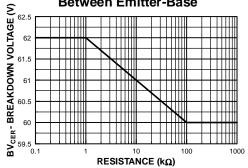
(continued)

Typical Characteristics (continued)

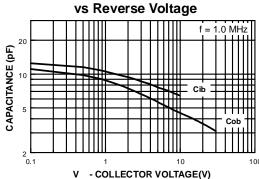
Collector-Cutoff Current vs Ambient Temperature



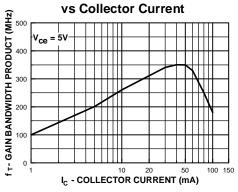
Collector-Emitter Breakdown Voltage with Resistance Between Emitter-Base



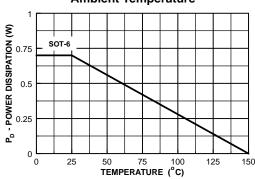
Input and Output Capacitance

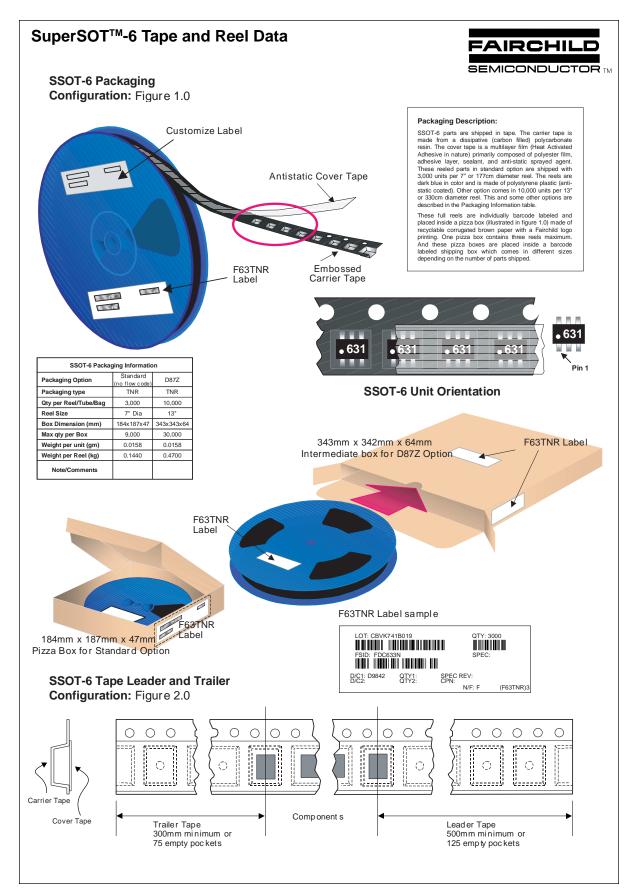


Gain Bandwidth Product



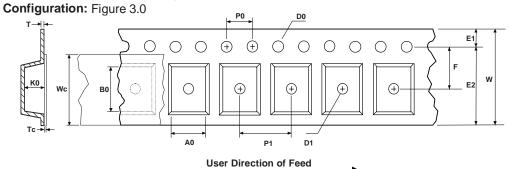
Power Dissipation vs Ambient Temperature







SSOT-6 Embossed Carrier Tape



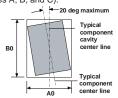
Dimensions are in millimeter	

	Dimensions are in millimeter													
Pkg type	Α0	В0	w	D0	D1	E1	E2	F	P1	P0	K0	Т	Wc	Тс
SSOT-6 (8mm)	3.23 +/-0.10	3.18 +/-0.10	8.0 +/-0.3	1.55 +/-0.05	1.125 +/-0.125	1.75 +/-0.10	6.25 min	3.50 +/-0.05	4.0 +/-0.1	4.0 +/-0.1	1.37 +/-0.10	0.255 +/-0.150	5.2 +/-0.3	0.06 +/-0.02

Notes: A0, B0, and K0 dimensions are determined with respect to the EIA/Jedec RS-481 rotational and lateral movement requirements (see sketches A, B, and C).



Sketch A (Side or Front Sectional View)
Component Rotation

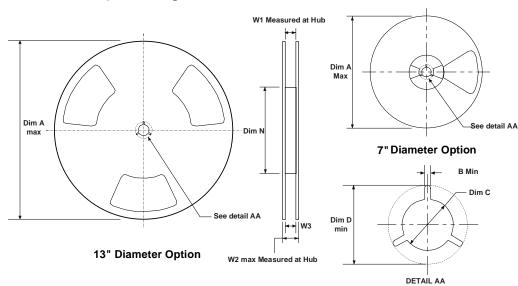


Sketch B (Top View)
Component Rotation



Sketch C (Top View)
Component lateral movement

SSOT-6 Reel Configuration: Figure 4.0

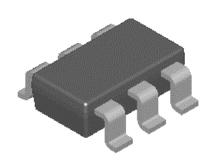


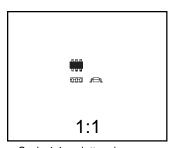
	Dimensions are in inches and millimeters									
Tape Size	Reel Option	Dim A	Dim B	Dim C	Dim D	Dim N	Dim W1	Dim W2	Dim W3 (LSL-USL)	
8mm	7" Dia	7.00 177.8	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	2.165 55	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	
8mm	13" Dia	13.00 330	0.059 1.5	512 +0.020/-0.008 13 +0.5/-0.2	0.795 20.2	4.00 100	0.331 +0.059/-0.000 8.4 +1.5/0	0.567 14.4	0.311 - 0.429 7.9 - 10.9	

SuperSOT[™]-6 Package Dimensions



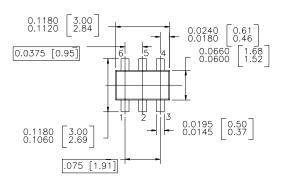
SuperSOT™-6 (FS PKG Code 31, 33)

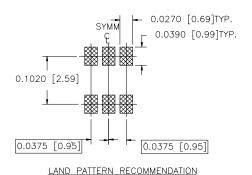




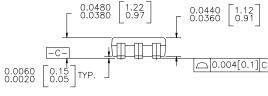
Scale 1:1 on letter size paper
Dimensions shown below are in:
inches [millimeters]

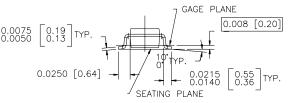
Part Weight per unit (gram): 0.0158





CONTROLLING DIMENSION IS INCH VALUES IN [] ARE MILLIMETERS





NOTES: UNLESS OTHERWISE SPECIFIED

1.0 STANDARD LEAD FINISH : 150 MICROINCHES 93.81 MICROMETERS) MINIMUM TIN / LEAD (SOLDER) ON COPPER.

 $2.0\ \mathsf{NO}\ \mathsf{JEDEC}\ \mathsf{REGISTRATION}\ \mathsf{AS}\ \mathsf{OF}\ \mathsf{JULY}\ 1996$

SUPER SOT 6 LEADS

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No Identification Needed	Full Production	This datasheet contains final specifications. Fairchild Semiconductor reserves the right to make changes at any time without notice in order to improve design.
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